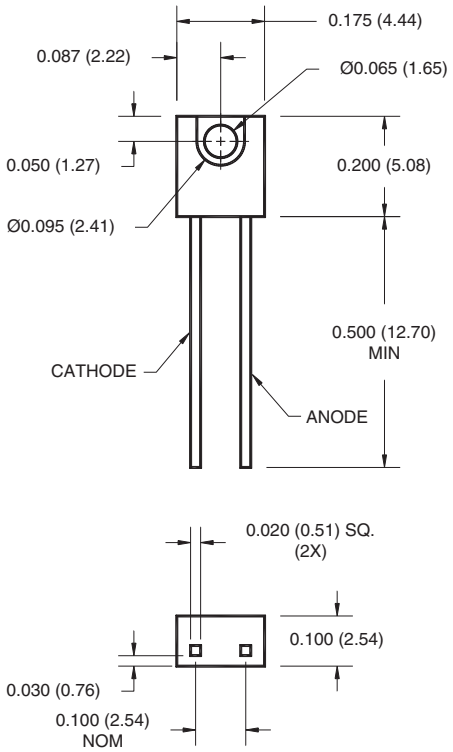
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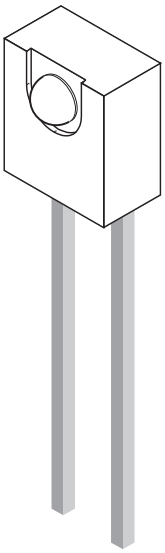
PLASTIC INFRARED LIGHT EMITTING DIODE

QEE113

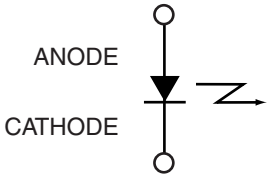
PACKAGE DIMENSIONS



NOTES:
1. Dimensions for all drawings are in inches (mm).
2. Tolerance of ± .010 (.25) on all non-nominal dimensions unless otherwise specified.



SCHEMATIC



DESCRIPTION

The QEE113 is a 940 nm GaAs LED encapsulated in a medium wide angle, plastic sidelooker package.

FEATURES

- λ= 940 nm
- Package Type = Sidelooker
- Chip Material = GaAs
- Matched Photosensor: QSE113
- Medium Wide Emission Angle, 50°
- Package Material: Clear Epoxy
- High Output Power
- Gray stripe on the top side

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ABSOLUTE MAXIMUM RATINGS (T_A = 25°C unless otherwise specified)			
Parameter	**Symbol**	**Rating**	**Unit**
Operating Temperature	T_{OPR}	-40 to +100	°C
Storage Temperature	T_{STG}	-40 to +100	°C
Soldering Temperature (Iron)(2,3,4)	T_{SOL-I}	240 for 5 sec	°C
Soldering Temperature (Flow)(2,3)	T_{SOL-F}	260 for 10 sec	°C
Continuous Forward Current	I_F	50	mA
Reverse Voltage	V_R	5	V
Power Dissipation(1)	P_D	100	mW

NOTES:
1. Derate power dissipation linearly 1.33 mW/°C above 25°C.
2. RMA flux is recommended.
3. Methanol or isopropyl alcohols are recommended as cleaning agents.
4. Soldering iron 1/16" (1.6 mm) minimum from housing.

ELECTRICAL / OPTICAL CHARACTERISTICS (T_A =25°C)						
Parameter	**Test Conditions**	**Symbol**	**Min**	**Typ**	**Max**	**Units**
Peak Emission Wavelength	I_F = 100 mA	λ_{PE}	—	940	—	nm
Emission Angle	I_F = 100 mA	2Θ1/2	—	50	—	Deg.
Forward Voltage	I_F = 100 mA, tp = 20 ms	V_F	—	—	1.5	V
Reverse Current	V_R = 5 V	I_R	—	—	10	µA
Radiant Intensity	I_F = 100 mA, tp = 20 ms	I_E	3	—	12	mW/sr
Rise Time	I_F = 100 mA	t_r	—	1000	—	ns
Fall Time		t_f	—	1000	—	ns

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QEE113

Fig.1 Normalized Radiant Intensity vs. Forward Current

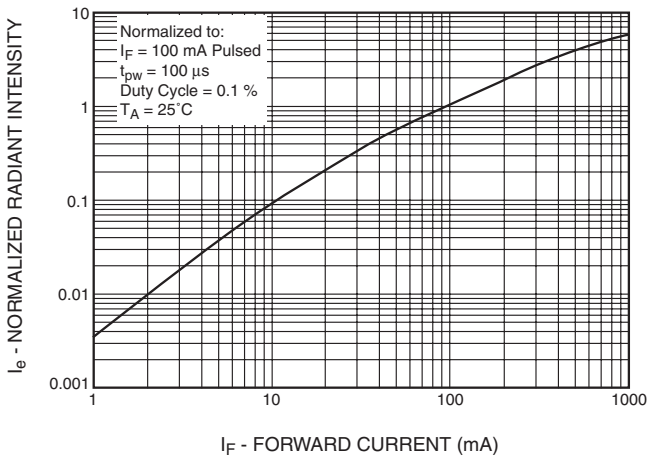


Fig.2 Coupling Characteristics of QEE113 And QSE113

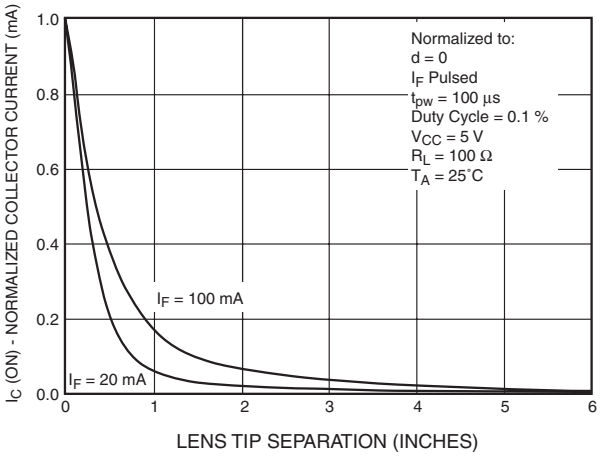


Fig.3 Forward Voltage vs. Ambient Temperature

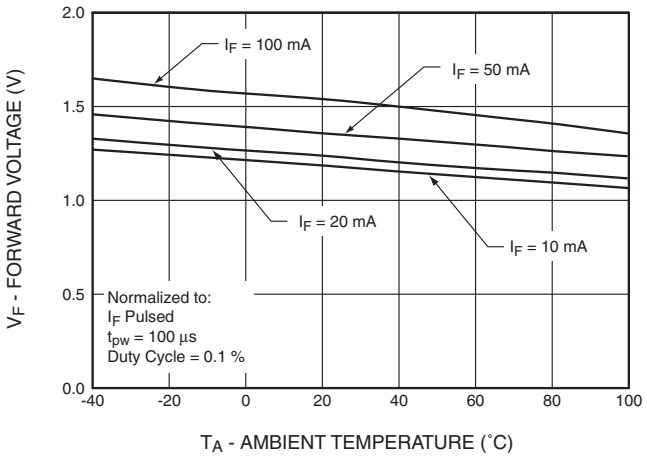


Fig. 4 Normalized Intensity vs. Wavelength

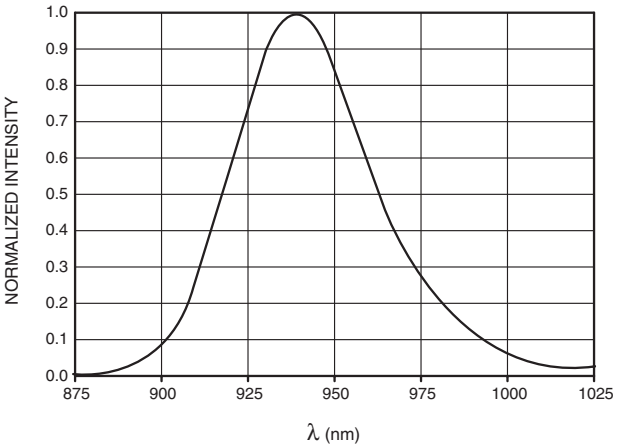
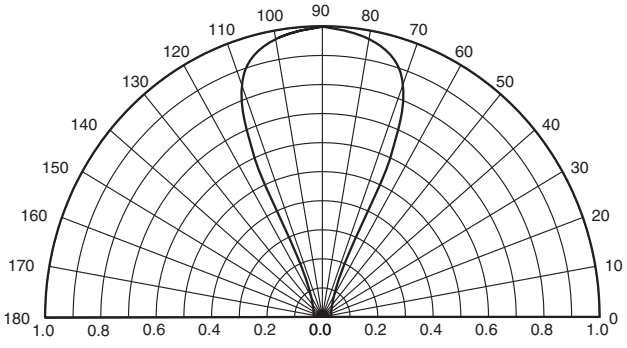


Fig. 5 Radiation Diagram



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QEE113

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